

Medium Power Transistor

(32V, 0.8A)

L2SD1781K*LT1

●Features

- 1) Very low $V_{CE(sat)}$.
 $V_{CE(sat)} < 0.4\text{ V (Typ.)}$
($I_C / I_B = 500\text{mA} / 50\text{mA}$)
- 2) High current capacity in compact package.
- 3) Complements the L2SB1197K*LT1
- 4) Pb Free Package is Available.

●Structure

Epitaxial planar type
NPN silicon transistor

●Absolute maximum ratings ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Limits	Unit
Collector-base voltage	V_{CBO}	40	V
Collector-emitter voltage	V_{CEO}	32	V
Emitter-base voltage	V_{EBO}	5	V
Collector current	I_C	0.8	A (DC)
		1.5	A (Pulse) *
Collector power dissipation	P_C	200	mW
Junction temperature	T_j	150	$^\circ\text{C}$
Storage temperature	T_{stg}	$-55 \sim +150$	$^\circ\text{C}$

* Single pulse $P_w = 100\text{ms}$

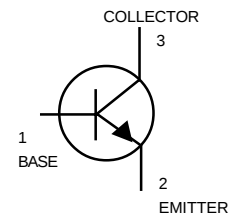
ORDERING INFORMATION

Device	Marking	Shipping
L2SD1781KQLT1	AFQ	3000 Tape & Reel
L2SD1781KQLT1G	AFQ(Pb-Free)	3000 Tape & Reel
L2SD1781KRLT1	AFR	3000 Tape & Reel
L2SD1781KRLT1G	AFR(Pb-Free)	3000 Tape & Reel

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SOT-23 /TO-236AB



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●Electrical characteristics (Ta = 25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Collector-base breakdown voltage	BV_{CBO}	40	—	—	V	$I_C = 50 \mu A$
Collector-emitter breakdown voltage	BV_{CEO}	32	—	—	V	$I_C = 1mA$
Emitter-base breakdown voltage	BV_{EBO}	5	—	—	V	$I_E = 50 \mu A$
Collector cutoff current	I_{CBO}	—	—	0.5	μA	$V_{CB} = 20V$
Emitter cutoff current	I_{EBO}	—	—	0.5	μA	$V_{EB} = 4V$
Collector-emitter saturation voltage	$V_{CE(sat)}$	—	—	0.4	V	$I_C/I_B = 500mA/50mA$
DC current transfer ratio	h_{FE}	120	—	390	—	$V_{CE} = 3V, I_C = 100mA$
Transition frequency	f_T	—	150	—	MHz	$V_{CE} = 5V, I_E = -50mA, f = 100MHz$
Output capacitance	C_{ob}	—	10	—	pF	$V_{CB} = 10V, I_E = 0A, f = 1MHz$

●DEVICE MARKING

L2SD1781KQLT1=AFQ L2S1781KRLT1=AFR

Item	Q	R
h_{FE}	120~270	180~390

●Electrical characteristic curves

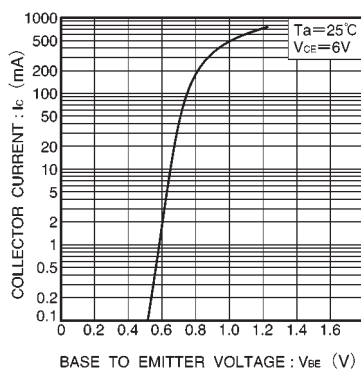


Fig.1 Grounded emitter propagation characteristics

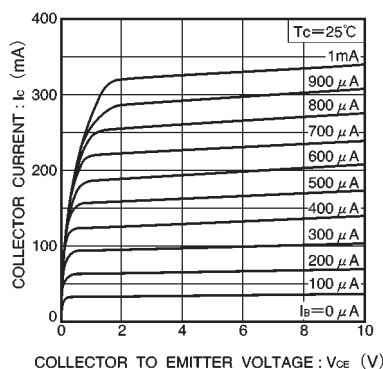


Fig.2 Grounded emitter output characteristics

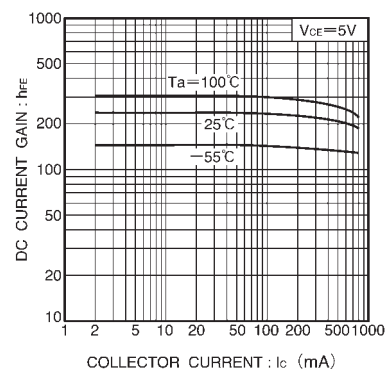


Fig.3 DC current gain vs. collector current

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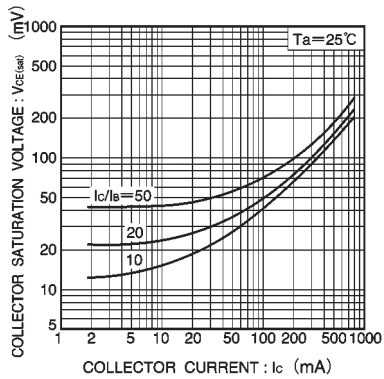


Fig.4 Collector-emitter saturation voltage vs. collector current (I)

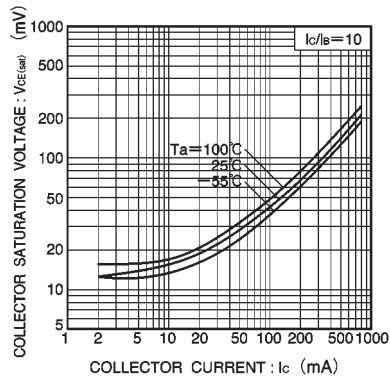


Fig.5 Collector-emitter saturation voltage vs. collector current (II)

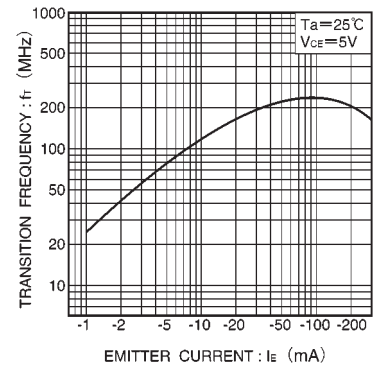


Fig.6 Gain bandwidth product vs. emitter current

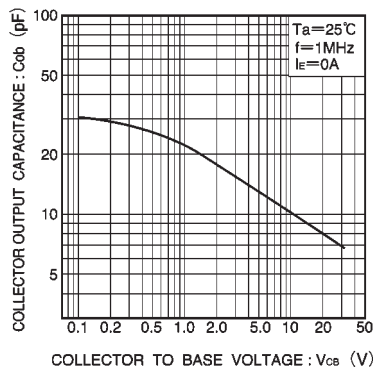


Fig.7 Collector output capacitance vs. collector-base voltage

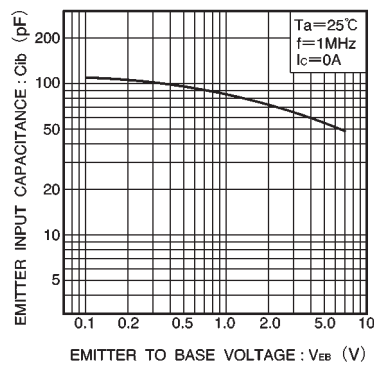
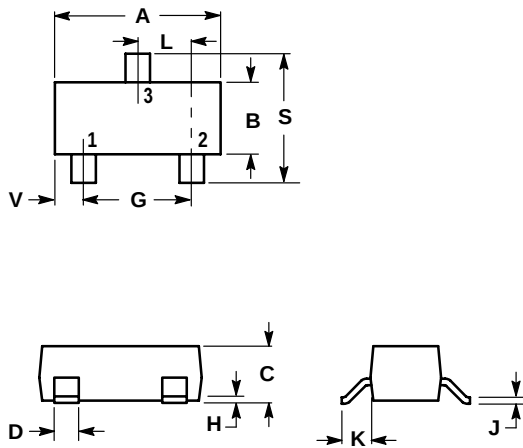


Fig.8 Emitter input capacitance vs. emitter-base voltage

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NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI
Y14.5M, 1982.
- CONTROLLING DIMENSION: INCH.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.1102	0.1197	2.80	3.04
B	0.0472	0.0551	1.20	1.40
C	0.0350	0.0440	0.89	1.11
D	0.0150	0.0200	0.37	0.50
G	0.0701	0.0807	1.78	2.04
H	0.0005	0.0040	0.013	0.100
J	0.0034	0.0070	0.085	0.177
K	0.0140	0.0285	0.35	0.69
L	0.0350	0.0401	0.89	1.02
S	0.0830	0.1039	2.10	2.64
V	0.0177	0.0236	0.45	0.60

- PIN 1. BASE
2. EMITTER
3. COLLECTOR

